

PNP Silicon Epitaxial Transistor

KSB834W

Features

- Complement to KSD880W
- This is a Pb-Free Device

Applications

• Low Frequency Power Amplifier

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-7	V
I _C	Collector Current	-3	Α
Ι _Β	Base Current	-0.5	Α
Pc	P _C Collector Dissipation (T _C = 25°C)		W
Pc	P _C Collector Dissipation (T _A = 25°C)		W
TJ	T _J Junction Temperature		°C
T _{STG} Storage Temperature		−55 ~ 150	°C

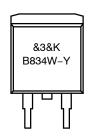
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



- 1. Base
- 2. Collector
- 3. Emitter

D²PAK-3 (TO-263, 3-LEAD) CASE 418AJ

MARKING DIAGRAM



&3 = Date Code Format &K = Lot Run Traceability Code B834W-Y = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
KSB834WYTM	D2PAK-3 (Pb-Free)	800 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

KSB834W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Test Condition	Min	Тур	Max	Unit
I _{CBO}	Collector Cut-off Current	$V_{CB} = -60 \text{ V}, I_{E} = 0$			-100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -7 \text{ V}, I_{C} = 0$			-100	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -50$ mA, $I_{\rm B} = 0$	-60			V
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} = -5 V, I _C = -0.5 A V _{CE} = -5 V, I _C = -3 A	60 20		200	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$		-0.5	-1	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} = -5 V, I _C = -0.5 A		-0.7	-1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -5 \text{ V}, I_{C} = -0.5 \text{ A}$		9		MHz
C _{cb}	Collector Output Capacitance	V _{CB} = -10 V, I _E = 0, f = 1 MHz		150		pF
t _{ON}	Turn On Time	$V_{CC} = -30 \text{ V}, I_C = -1 \text{ A}, I_{B1} = -I_{B2} = -0.2 \text{ A},$		0.4		μs
t _{STG}	Storage Time	$R_L = 30 \Omega$		1.7		μs
t _F	Fall Time			0.5		μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

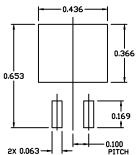
\mathbf{h}_{FE} CLASSIFICATION

Classification	0	Y
h _{FE1}	60 ~ 120	100 ~ 200



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DATE 11 MAR 2021



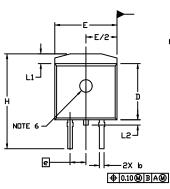
RECOMMENDED
MOUNTING FOOTPRINT

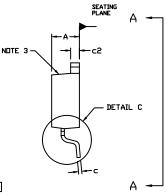
For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Table Semiconductor Manual Table 17 PROBLED

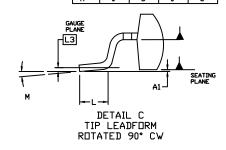
NOTES

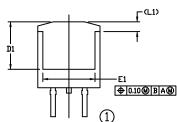
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. CHAMFER OPTIONAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE.
 THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST
 EXTREMES OF THE PLASTIC BODY AT DATUM H.
- 5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
- 6. OPTIONAL MOLD FEATURE.
- 7. ①,② ... DPTIONAL CONSTRUCTION FEATURE CALL DUTS.

	INCHES		MILLIN	ETERS	
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.06	4.83	
A1	0.000	0.010	0.00	0.25	
b	0.020	0.039	0.51	0.99	
С	0.012	0.029	0.30	0.74	
c2	0.045	0.065	1.14	1.65	
D	0.330	0.380	8.38	9.65	
D1	0.260		6.60		
E	0.380	0.420	9.65	10.67	
E1	0.245		6.22		
e	0.100 BSC		2.54	2.54 BSC	
Н	0.575	0.625	14.60	15.88	
L	0.070	0.110	1.78	2.79	
L1		0.066		1.68	
L2		0.070		1.78	
L3	0.010	BSC	0.25 BSC		
м	N*	8*	n•	8.	

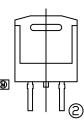


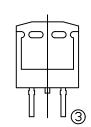


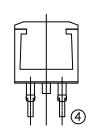




VIEW A-A







VIEW A-A

OPTIONAL CONSTRUCTIONS

GENERIC MARKING DIAGRAMS*

XX
XX
XXXXXXXX
AWLYWWG
AYWW
AYWW
AKA

IC Standard Rectifier SSG

XXXXXX = Specific Device Code

 A
 = Assembly Location

 WL
 = Wafer Lot

 Y
 = Year

 WW
 = Work Week

 W
 = Week Code (SSG)

 M
 = Month Code (SSG)

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:

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